<table>
<thead>
<tr>
<th>Symbol</th>
<th>Full Form.</th>
</tr>
</thead>
<tbody>
<tr>
<td>a</td>
<td>Active solar cell area.</td>
</tr>
<tr>
<td>b</td>
<td>Impact parameter.</td>
</tr>
<tr>
<td>c</td>
<td>Velocity of light.</td>
</tr>
<tr>
<td>Dp</td>
<td>Diffusion coefficient due to holes.</td>
</tr>
<tr>
<td>d</td>
<td>Oxide thickness.</td>
</tr>
<tr>
<td>Nss</td>
<td>Surface state density.</td>
</tr>
<tr>
<td>e</td>
<td>Electronic charge.</td>
</tr>
<tr>
<td>Ed</td>
<td>Displacement energy.</td>
</tr>
<tr>
<td>Isc0</td>
<td>Short circuit current before irradiation.</td>
</tr>
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<tr>
<td>IL</td>
<td>Load current.</td>
</tr>
<tr>
<td>ID</td>
<td>Diode dark current.</td>
</tr>
<tr>
<td>Iph</td>
<td>Photogenerated current.</td>
</tr>
<tr>
<td>Im</td>
<td>Maximum current.</td>
</tr>
<tr>
<td>Jsc</td>
<td>Short circuit current density</td>
</tr>
<tr>
<td>K</td>
<td>Boltzman's constant.</td>
</tr>
<tr>
<td>KL</td>
<td>Damage coefficient.</td>
</tr>
<tr>
<td>Lpo</td>
<td>Initial minority carrier diffusion length.</td>
</tr>
<tr>
<td>Lp</td>
<td>Hole diffusion length.</td>
</tr>
<tr>
<td>m0</td>
<td>Rest mass of electron.</td>
</tr>
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</table>
Absorption coefficient.

Dielectric constant.

Nuclear mass.

Rest mass of electron

Diode ideality factor.

Effective density of states in valence band.

Effective density of holes in conduction band.

Net trap charge density

Electron momentum.

Total charge in the surface states.

Space charge density.

Charge due to uncompensated donors.

Charge due to holes in valence band.

Recombination speed.

Depletion layer width.

Rydberg energy.

Bohr radius.

Energy bandgap.

Photon flux.

Electron affinity.

Attenuation constant.

Surface state capacitance.

Insulator capacitance.

Depletion layer capacitance.
Defect density.

Number of lattice atoms per unit volume.

Incident solar intensity.

Series resistance.

Shunt resistance.

Fill factor.

Temperature.

Image lowering force.

Relative velocity.

Interaction potential.

Thermal velocity.

Load voltage.

Voltage drop across the junction.

Open circuit voltage.

Atomic number.

Capture crosssection for holes.

Displacement crosssection.

Differential scattering crosssection.

Scattering angle.

Recombination time constant.

Defect control life time.

Minority carrier lifetime before irradiation.

Effective minority carrier lifetime.

Barrier height.

Radiation fluence.

Efficiency.
\( \mathcal{E} \)  
Electric field strength in the semiconductor.

\( q_m \)  
Charge due to electrons on the surface of the metal.

\( V_d \)  
Diffusion voltage.

\( V_i \)  
Built in potential.

\( \lambda_d \)  
Space charge width.

\( \varepsilon_0 \)  
Permitivity of free space.

\( \varepsilon_i \)  
Permitivity of insulator.

\( \varepsilon_s \)  
Permitivity of the semiconductor.